

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Inventor(s):** Farnworth et al.

**Patent No.:** 6,831,475 B2

**Issued:** December 14, 2004

**For:** DEVICE AND METHOD FOR  
ISOLATING A SHORT-CIRCUITED  
INTEGRATED CIRCUIT (IC) FROM  
OTHER ICs ON A SEMICONDUCTOR  
WAFER

**Attorney Docket No.:** 2269-3038.3US

VIA ELECTRONIC FILING  
July 30, 2007

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT  
OFFICE MISTAKES (37 C.F.R. § 1.322)**

Attn.: Certificate of Corrections Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

It is noted that several errors appear in this patent of a typographical nature. These errors are due to mistakes in printing on the part of the U.S. Patent and Trademark Office, and occurred through no fault of the Applicants. A certificate of correction in the form attached hereto is requested.

Please send the Certificate to:

Name: James R. Duzan  
Address: TraskBritt  
P.O. Box 2550  
Salt Lake City, Utah 84110

Attached hereto in duplicate is Form PTO/SB/44 with at least one copy being suitable for printing.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "James R. Duzan". The signature is fluid and cursive, with the first name "James" being more prominent.

James R. Duzan  
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Date: July 30, 2007  
JRD/csw

Enclosures: PTO/SB/44

Document in ProLaw

**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

PATENT NO : 6,831,475 B2 Page 1 of 1  
APPLICATION NO. : 10/690,496  
ISSUE DATE : December 14, 2004  
INVENTOR(S) : Warren M. Farnworth, William K. Waller, Leland R. Nevill, Raymond J. Beffa,  
and Eugene H. Cloud

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

**On the title page:**

In ITEM (54) "Title",

change "DEVICE AND METHOD FOR ISOLATING  
A SHORT-CIRCUITED INTEGRATED CIRCUIT  
(IC) FROM OTHER ICS ON A SEMICONDUCTOR  
WAFER" to --DEVICE AND METHOD FOR  
ISOLATING A SHORT-CIRCUITED INTEGRATED  
CIRCUIT (IC) FROM OTHER ICs ON A  
SEMICONDUCTOR WAFER--

**In the specification:**

COLUMN 1, LINE 3,

change "(IC) FROM OTHER ICS ON A" to  
--(IC) FROM OTHER ICs ON A --

**MAILING ADDRESS OF SENDER:**

James R. Duzan  
TRASKBRITT  
230 South 500 East, Suite 300  
Salt Lake City, Utah 84102 USA

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS.  
**SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

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